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SOFT ERROR RESISTANT MEMORY CELL AND METHOD OF MANUFACTURE

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Inventors: **Bo Jin, Ahmad Chatila and Kaichiu Wong**

SOFT ERROR RESISTANT MEMORY CELL AND METHOD OF MANUFACTURE

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TECHNICAL FIELD

The present invention relates generally to integrated circuits and, more
particularly to a circuit for reducing a soft-error rate in a semiconductor memory device,
10 and a method of manufacturing such a circuit.

BACKGROUND OF THE INVENTION

Semiconductor memory devices are typically manufactured with circuits, such as
redundancy circuits, to address defects that can arise from uncontrollable
15 manufacturing process variations, and the like. Unfortunately, semiconductor memory
devices are still vulnerable to errors that may arise out of the operating environment and
conditions, such as "soft" errors.

"Soft" errors are random errors that can appear in a memory device that are not
related to any defect. Soft errors are most often attributed, either directly or indirectly, to
20 sub-atomic particles. More particularly, many soft errors are believed to result from
alpha particles traveling through a semiconductor substrate and generating electron
hole pairs. Alpha particles may be generated by the decay of elements (e.g., uranium,
thorium) or cosmic ray events, for example.

In a soft-error event, generated electron hole pairs can cause a change in state

of the data stored within a memory device. For example, in the case of a dynamic random access memory (DRAM) type cell, generated electron hole pairs may result in loss of charge from a storage capacitor. In the case of a latch-based static RAM (SRAM) type cell, the cell may “flip”, resulting in the opposite logic value being stored.

- 5 Soft errors in semiconductor devices are often described in terms of a soft-error rate (SER). An SER can be an indication of an integrated circuit’s degree of susceptibility to soft-error events.

One way of reducing the SER in DRAM devices can be to increase the capacitance of a storage cell. However, this approach has disadvantages that may
10 include increased current consumption and/or larger memory cell sizes.

Other approaches to reducing the SER of semiconductor devices include forming a thick polymer coating and/or a phosphosilicate glass (PSG) type of layer on top of the device. Such a coating may act to absorb some soft-error particles before they can impact the memory cells. Also, materials used to package devices may be
15 manufactured to have low levels of radioactive impurities so as to reduce the possible sources of unwanted particles.

Unfortunately, as semiconductor memory devices continue to shrink in size, the number of electron hole pairs necessary to induce a soft error can be correspondingly smaller. Thus, it remains a continuing goal to reduce the soft error rate (SER) of
20 semiconductor memory devices.

SUMMARY OF THE INVENTION

The present invention can include a memory cell having a first node for storing a

first potential and a second node for storing a second potential. In addition, the memory cell can include a capacitor having plates coupled between the first node and second node. A portion of at least one plate of the capacitor can be formed from a first interconnect wiring that interconnects circuit components of the memory cell.

5 The inclusion of a capacitor between data storage nodes can increase a memory cell resistance to soft error events (i.e., reduce a soft error rate).

 According to one aspect of the embodiments, a memory cell may further include a first inverter having an input coupled to the first node and an output coupled to the second node. In addition, a second inverter can have an input coupled to the second
10 node and an output coupled to the first node. A first node can store a true data value and a second node can store a complementary data value.

 In this way, a memory cell may include complementary data nodes. Such an arrangement may be particularly applicable to higher speed memory devices, such as static random access memories (SRAM), dual port RAMs, and content address
15 memories (CAM), to name just a few.

 According to another aspect of the embodiments, a memory cell may further include a first access transistor coupled to the first node, and a second access transistor coupled to the second node.

 Such an arrangement can allow for access to both data nodes.

20 According to another aspect of the embodiments, a memory cell may further include transistor gates formed from a gate layer and a first conductive interconnect wiring formed over the gate layer. A first conductive interconnect wiring can include a plurality of conductive layers, at least one of the conductive layers forming a portion of a

first plate of the capacitor.

In this way, a capacitor can be formed from memory cell wiring utilized to connect memory cell circuit components. Such an arrangement may advantageously utilize existing structures within a memory cell.

5 According to another aspect of the embodiments, a first conductive interconnect wiring can include a bottom conductive layer, a dielectric layer formed over the bottom conductive layer, and a top conductive layer formed over the dielectric layer. The top conductive layer can form at least a portion of a first plate of the capacitor.

10 In this way, a first conductive interconnect wiring can advantageously include a built-in capacitor dielectric.

 According to another aspect of the embodiments, a second conductive interconnect wiring can be formed over the first conductive interconnect wiring. The second conductive wiring can form at least a portion of a second plate of the capacitor.

15 According to another aspect of the embodiments, a second conductive interconnect wiring can include titanium. Further, a top conductive layer of the first conductive interconnect wiring can include titanium, and a bottom conductive layer of the first conductive interconnect wiring can include titanium nitride.

20 The present invention may also include a method of forming a capacitor in an integrated circuit. The method can include depositing an insulating layer over a plurality of capacitor structures. Each capacitor structure can include a dielectric layer disposed between a first interconnect layer and a second interconnect layer. The method may also include forming a recess in the insulating layer according to a capacitor mask pattern. Such a recess can expose a second interconnect layer of at least two capacitor

structures. A third interconnect layer can then be formed within the recess that is in electrical contact with the exposed second interconnect layers of the at least two capacitor structures.

According to another aspect of the embodiments, an insulating layer can include
5 silicon oxide.

According to another aspect of the embodiments, a third interconnect layer can include titanium.

According to another aspect of the embodiments, a method may further include, prior to depositing the insulating layer, forming a first interconnect layer, forming a
10 dielectric layer over the first interconnect layer, and forming a second interconnect layer over the dielectric layer. An etching can then be performed that etches through the first interconnect layer, the dielectric layer, and the second interconnect layer to form capacitor structures.

In this way, a first interconnect layer can be patterned to form, not only an
15 interconnect pattern, but capacitor structures as well. The capacitor structures can subsequently be connected to form a built-in capacitor for a circuit, such as a memory cell.

According to another aspect of the embodiments, a first interconnect layer can comprise titanium nitride, and a second interconnect layer can comprise titanium.

According to another aspect of the embodiments, a method may further include,
20 after forming the capacitor structures, depositing a spacer insulating layer over the capacitor structures, and anisotropically etching the spacer insulating layer to form insulating spacers on side surfaces of the capacitor structures.

In this way, a spacer can be formed that can isolate a bottom layer of a first interconnect wiring from a top layer. Such an arrangement can make it easier to make a conductive connection with a top conductive layer while maintaining electrical isolation from a bottom conductive layer of the interconnect wiring.

5 According to another aspect of the embodiments, a step of forming a recess in the insulating layer can include etching a portion of the first insulating layer. In addition, after forming the third interconnect layer, a chemical-mechanical polishing can remove portions of the third interconnect layer outside of the recess.

In this way, a remaining portion of a third interconnect layer can form a capacitor plate portion that is self-aligned with respect to the recess.

The present invention may also include a method of forming an integrated circuit memory cell. Such a method can include forming a first interconnect wiring that electrically connects a plurality of transistor gates to transistor diffusion regions, the first interconnect wiring pattern can include at least one dielectric layer between top and bottom conductive layers. The method may also include forming a second interconnect layer over the first interconnect wiring that is in electrical contact with the top conductive layers to form a capacitor. The capacitor can include a first plate comprising the top conductive layer, a second plate comprising the second interconnect layer, and a capacitor dielectric comprising the at least one dielectric layer.

In this way, a capacitor can be formed for a memory cell that advantageously incorporates a first interconnect wiring pattern.

10 According to another aspect of the embodiments, forming a first interconnect wiring can include forming the bottom conductive layer having a thickness of no more

than about 1000 angstroms, forming a dielectric layer having a total thickness of less than about 80 angstroms, and forming a top conductive layer having a thickness of no more than about 300 angstroms. The method may also include etching through the bottom conductive layer, at least one dielectric layer and the top conductive layer according to a first wiring pattern.

According to another aspect of the embodiments, a method may also include forming insulating sidewalls on the sides of the first interconnect wiring.

According to another aspect of the embodiments, forming insulating sidewalls can also include depositing a layer of silicon nitride having a thickness of no more than about 500 angstroms, and anisotropically etching the layer of silicon nitride.

According to another aspect of the embodiments, a first interconnect wiring can include a first wiring portion that electrically connects the gate of a first memory cell transistor to a source/drain region of a second memory cell transistor, and a second wiring portion that electrically connects a gate of the second memory cell transistor to a source/drain region of the first memory cell transistor.

According to another aspect of the embodiments, first and second wiring portions can be formed on an interconnect insulator layer. A first wiring portion can be electrically connected to the gate of the first memory cell transistor by a first local contact that extends through the interconnect insulator layer. A second wiring portion can be electrically connected to the gate of the second memory cell transistor by a second local contact that extends through the interconnect insulator layer.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic diagram of a first embodiment of the present invention.

FIG. 2 is a schematic diagram of a second embodiment of the present invention.

FIG. 3 is a flow diagram of a method of manufacturing a capacitor according to
5 one embodiment of the present invention.

FIGS. 4A to 4E are side cross sectional views illustrating the method of FIG. 3.

FIG. 5 is a flow diagram of another method of manufacturing a capacitor
according to an embodiment of the present invention.

FIGS. 6A to 6K are side cross sectional views illustrating the method of FIG. 6.

FIG. 7A is top plan view showing the layout of a static random access memory
10 (SRAM) cell according to one particular embodiment of the present invention.

FIG. 7B is a side cross sectional view taken along line B-B of FIG. 7A.

DETAILED DESCRIPTION

15 Various embodiments of the present invention will now be described in detail with
reference to a number of drawings. The embodiments include a memory cell circuit
having a capacitor for reducing a soft error rate, as well as a method of manufacturing
such a capacitor.

A first embodiment of the present invention includes a memory cell and is set
20 forth in FIG. 1 and designated by the general reference character **100**. A first
embodiment **100** can include a memory cell having a built-in capacitor for increasing a
capacitance between data storage nodes. Such an increased capacitance can reduce
a soft-error rate (SER) by improving a node's resistance to being charged/discharged in

response to a soft error event (e.g., spontaneous generation of electron-hole pairs). In the very particular example of FIG. 1, a memory cell can include a static random access memory (SRAM) type memory cell. However, the present invention should not necessarily be construed as being limited to any particular type of memory cell.

5 Referring to FIG. 1, a first embodiment **100** can include a first inverter **102** and second inverter **104** arranged in a cross-coupled configuration, with an output of a first inverter **102** being connected to an input of a second inverter **104**, and vice versa. In such an arrangement, a resulting SRAM cell can include a first storage node **106** for storing a first data value (a “true” value) and a second storage node **108** for storing a
10 complementary data value. Thus, according to the data value being stored, a first storage node **106** will be at one potential (e.g., a high voltage) while a second storage node **108** will be at another potential (e.g., a low voltage).

Unlike conventional 6-T SRAM cells, a first embodiment **100** may further include a capacitor **110** coupled between first storage node **106** and second storage node **108**.

15 As noted above, storage nodes (**106** and **108**) can be at different potentials in operation. A capacitor **110** can help maintain such a potential difference in the event either storage node (**106** and **108**) is temporarily disturbed due to a soft error event. That is, a transient response at such nodes (dV/dt) would be slowed due to such a capacitance.

It is understood that a capacitor **110** may be composed of one set of opposing
20 conductive layers separated by a dielectric, or may be composed of multiple such structures. That is, a capacitor **110** may physically include a single capacitor structure, or multiple capacitor structures arranged in parallel and/or in series.

As illustrated in FIG. 1, within inverter **102**, gates of transistors M1 and M3 can

be connected to a drain-drain connection between transistors M2 and M4. Such an interconnection can be accomplished by way of a local interconnect wiring. Similarly, gates of transistors M2 and M4 can be connected to a drain-drain connection between transistors M1 and M3 by such a local interconnect wiring. At the same time, the same
5 interconnect wiring can form plates for capacitor **110**.

More particularly, a capacitor **110** can have one plate connected to a gate of transistor M2 and transistor M4 of inverter **104** by way of an interconnect wiring. Another plate of capacitor **110** can be connected to a gate of transistor M1 and M3 of inverter **102** by such an interconnect wiring. Transistors M1 and M2 can be n-channel
10 insulated gate field effect transistors (referred to herein generally as MOS transistors) and transistors M3 and M4 can be p-channel MOS transistors.

In this way, a capacitor **110** can be a "built-in" capacitor formed with interconnect wirings utilized to connect memory cell circuit components.

As will be described in more detail below, a local interconnect wiring can include
15 a patterned layer in combination with local contacts. Such local interconnect layers may be disposed above a gate layer. Preferably, one plate of capacitor **110** can be formed from one interconnect layer, while another is formed from a different interconnect layer.

A first embodiment **100** further includes a first access transistor M5 connected to a first storage node **106** and a second access transistor M6 connected to a second
20 storage node **108**. Access transistors (M5 and M6) can provide access to data values stored within memory cell **100**. Transistors M5 and M6 can be n-channel MOS transistors. In one particular arrangement, one or both of access transistors (M5 and M6) can connect the corresponding storage nodes (**106** and **108**) to bit lines (not shown

in FIG. 1).

While the embodiment of FIG. 1 shows the present invention implemented in a six transistor static random access memory (SRAM), the present invention should not be limited to such an application. As but one example, a four transistor SRAM

5 implementation is shown in FIG. 2.

FIG. 2 is a schematic diagram of a second embodiment of the present invention. FIG. 2 includes the same general components as FIG. 1. Accordingly, like components characters will be referred to by the same reference character, but with the first character being a "2" instead of a "1".

10 FIG. 2 differs from FIG. 1 in that p-channel transistors M3 and M4 are replaced by resistors R1 and R2.

Having described particular arrangements of a memory cell with a built-in capacitor for reducing soft-errors, a method of manufacturing such a built-in capacitor will now be described with reference to FIGS. 3 and 4A to 4E. FIG. 3 is a flow diagram
15 of a method for forming a built-in capacitor within a memory cell. FIGS. 4A to 4E are side cross sectional views of a portion of a semiconductor device illustrating the method of FIG. 3. In the following description, it is understood that "top", "bottom", "above", "below", "over", "under" and the like, are illustrative relative terms and should not be construed as limiting to particular device orientations or arrangements.

20 Referring now to FIG. 3, a method according to one embodiment is designated by the general reference character **300** can include forming a first interconnect wiring layer with a top conductive layer, middle dielectric layer and bottom conductive layer (step **302**).

One example of a semiconductor device following a step **302** is shown in FIG.

4A. A semiconductor device can include a substrate **400** in which memory cell circuit elements can be formed. Such elements may include, as but one example, transistor gate structures **402** and transistor source/drain regions **404**. An interconnect insulating layer **406** may be formed over a substrate. A local contact **408** can extend through interconnect insulating layer to make electrical contact with memory cell circuit elements.

FIG. 4A also shows a first interconnect layer **410** formed over interconnect insulating layer **406**. A first interconnect layer **410** can include a first conductive layer **412-a**, a dielectric layer **414**, and a second conductive layer **412-b**. Thus, a first conductive layer **412-a** can be a bottom layer, a dielectric layer **414** can be a middle layer, and a second conductive layer **412-b** can be a top layer.

FIG. 4A shows that unlike conventional interconnect layers, which are composed only of one or more conductive layers, a first interconnect layer of the embodiment shown can include at least one dielectric layer sandwiched between conductive film. As will be described later, such a dielectric layer **414** can serve as a capacitor dielectric.

Referring back to FIG. 3, a method **300** can further include patterning a first interconnect layer to form a first interconnect wiring (step **304**). It is understood that a first interconnect wiring can electrically interconnect memory cell circuit components.

One example of a semiconductor device following a step **304** is shown in FIG. 4B. First interconnect wiring **410** has been patterned resulting in interconnect capacitor structures **416-a** and **416-b**. Interconnect capacitor structures (**416-a** and **416-b**) can provide interconnection between memory cell circuit components. In addition, such

structures may also form capacitor structures, including conductive plates **412-a'** and **412-b'** on either side of a dielectric **414'**.

A method **300** can also include forming an interlayer insulating film over a first interconnect wiring (step **306**). One example of a semiconductor device following a step
5 **306** is shown in FIG. 4C. An interlayer insulating film **418** can be formed over interconnect capacitor structures (**416-a** and **416-b**).

A method **300** can further include removing an interlayer insulating film to expose a top conductive layer of interconnect capacitor structures. One example of a semiconductor device following such a step is shown in FIG. 4D. Such a step can
10 expose a top conductive layer **412-b'** of interconnect capacitor structures (**416-a** and **416-b**).

A method **300** can also include forming a third conductive layer in electrical contact with a top conductive layer of the first interconnect capacitor structures (step **310**).

One example of a semiconductor device following such a step is shown in FIG.
15 4E. After such a step, a third conductive layer **420** can provide a common plate in conjunction with top conductive layer **412-b'**. Resulting capacitors are shown as C1 and C2 in FIG. 4E. Such capacitors may be arranged in series or in parallel according to the configuration of interconnect capacitor structures (**416-a** and **416-b**). In the particular
20 example of FIG. 4E, capacitors C1 and C2 are connected in series.

In this way, a interconnect wiring (**416-a** and **416-b**) can provide both interconnect functions as well as a built-in capacitor structures for a memory cell.

Having described one embodiment method, a second more detailed embodiment

will now be described with reference to FIGS. 5 and 6A to 6K. FIG. 5 is a flow diagram of a method according to another embodiment. FIGS. 6A to 6K are side cross sectional views of a portion of a semiconductor device illustrating the method of FIG. 5. FIGS. 6A-6K illustrate the process steps and associated architecture that can be used to form a capacitor during the fabrication of a semiconductor device.

The method shown in FIG. 5 is designated by the general reference character **500** can include depositing a first conductive layer over a transistor gate layer (step **502**).

Referring to FIG. 6A, prior to a step **502**, a semiconductor device can include a silicon substrate **600**. An interconnect insulating layer **602** can be formed over substrate **600**. An interconnect insulating layer **602** may comprise silicon dioxide, preferably a phosphosilicate glass (PSG) layer. A "cap" insulating layer **604** can be formed on interconnect insulating layer **602**. A cap insulating layer **604** may comprise silicon dioxide, preferably an undoped silicate glass (USG) layer. A local interconnect (LI) contact **606** can be formed through interconnect insulating layer **602** and cap insulating layer **604** to a substrate **600** (and/or transistor gate layer, not shown in FIGS. 6A-6K).

An LI contact **606** may provide an electrical connection between a memory cell circuit element (e.g., a transistor gate or source/drain region) and an overlying interconnect wiring.

Referring still to FIG. 6A, following a step **502**, a first conductive layer **608** can be deposited on top of cap insulating layer **604**. A first conductive layer **608** may serve as a first local interconnect layer, by providing a first conductive connection layer for circuit

elements. A first conductive layer can include titanium nitride (TiN) deposited to a thickness within a range of about 100 angstroms (Å) to about 5000 Å, preferably about 1000 Å. Of course, while titanium nitride may have advantageous adhesion and diffusion barrier properties, a first conductive layer **608** should not be construed as
5 being limited to any particular material.

A dielectric layer may then be deposited (step **504**).

Referring to FIG. 6B, following a step **504**, a dielectric layer **610** can be deposited over a first conductive layer **608**. Such a step can form a dielectric of a built-in capacitor. Such a step may preferably include the deposition of a relatively thin layer of
10 silicon nitride. Such a silicon nitride layer can have a thickness within a range of about 20 Å to about 300 Å, preferably about 80 Å. A resulting capacitor structure can include a first conductive layer **608** as one terminal (or electrode or plate) and dielectric layer **610** as a capacitor dielectric for resulting capacitor structures.

A dielectric of deposited silicon nitride may be easily incorporated into a
15 manufacturing process, and provide a high dielectric constant. However, the present invention should not necessarily be construed as being limited to such a material.

A method **500** may further include depositing a second conductive layer (step **506**).

Referring to FIG. 6C, following a step **506**, a second conductive layer **612** can be
20 formed over dielectric layer **610**. Such a step can form a second terminal for resulting capacitor structures, and in addition, may be commonly patterned with first conductive layer **608** and dielectric layer **610** to form a first interconnect wiring that connects circuit elements to one another. In the particular example shown, a second conductive layer

612 can include titanium (Ti) deposited to a thickness within a range of about 80 Å to about 1500 Å, but preferably to about 300 Å. Of course, a second conductive layer **612** should not necessarily be construed as being limited to any particular material.

Once a first conductive layer, dielectric layer and second conductive layer have
5 been deposited, such layers may be etched to form a first interconnect wiring (step **508**).

Referring to FIG. 6D, following a step **508**, a first conductive layer **608**, dielectric layer **610** and second conductive layer **612** can be etched through to expose a cap insulating layer **604** and form a first interconnect wiring. Such a wiring can include a
10 number of segments, four of which are shown as **614-a**, **614-b**, **614-c** and **614-d**. Such an interconnect wiring (**614-a**, **614-b**, **614-c** and **614-d**) can provide electrical connection to/between circuit elements. For example, segment **614-b** is shown connected to substrate **600** by LI contact **606**.

However, unlike conventional interconnect wiring, first interconnect wiring
15 segments (**614-a**, **614-b**, **614-c** and **614-d**) can also form individual capacitor structures. For example, wiring segment **614-a** can form a capacitor structure having a first conductive layer portion **608'** as one plate, a dielectric layer portion **610'** as a capacitor dielectric, and a second conductive layer portion **612'** as another plate. In one very particular embodiment, two of these structures can be connected in series to form one
20 effective capacitance per SRAM cell, as will be described below.

After the formation of a first interconnect wiring, an insulating sidewall layer can be deposited over a first interconnect wiring (step **510**). Such a step can include depositing a layer of silicon nitride with a thickness in the range of 100 Å to 3500 Å,

preferably about 500 Å. Of course, the present invention should not necessarily be construed as limiting a sidewall layer to any particular material.

After depositing an insulating sidewall layer, such a layer can be anisotropically etched (step **512**).

5 Referring to FIG. 6E, following a step **512**, insulating spacers (two of which are shown as **616**) can be formed on side surfaces of first interconnect wiring segments (**614-a**, **614-b**, **614-c** and **614-d**). Spacers (e.g., **616**) can be formed in order to guard against possible shorts between first conductive layer portions (e.g., **608'**) and second conductive layer portions (**612'**). It is noted that in the example shown, a second
10 conductive layer portion (e.g., **612'**) of each first interconnect wiring segment can be exposed following a step **512**.

An interlayer insulating film can then be formed over a first interconnect wiring (step **514**).

Referring to FIG. 6F, following a step **514**, an interlayer insulating film **618** may
15 cover first interconnect wiring (**614-a**, **614-b**, **614-c** and **614-d**). Such a step may include depositing a layer of silicon oxide having a thickness in the range of about 500 Å to about 15000 Å, preferably about 3000 Å. Such a step may further include planarizing the deposited interlayer insulating film. Preferably, a chemical mechanical polish (CMP) step can form a substantially flat top surface on interlayer insulating film **618**.

20 A method **500** may then include removing a portion of the interlayer insulating film to form a recess and expose a second conductive layer (step **516**).

Referring to FIG. 6G, a semiconductor device following a step **516** is shown. Such a step can include etching with a capacitor open mask. A capacitor open mask

can define an area for a subsequently formed capacitor plate portion. After etching, a recess **620** can be formed within interlayer insulating film **618** that exposes second conductive layer portions **622-b** and **622-c** of selected first interconnect wiring segments. As but one example, a step **516** can include an oxide etch performed to stop
5 on second conductive layer portions (**622-b** and **622-c**). It is noted that spacers **612** can prevent first conductive layer portions (e.g., **608'**) from being exposed.

A third conductive layer may then be deposited (step **518**).

FIG. 6H shows a semiconductor device following a step **518**. A third conductive layer **624** can be formed over interlayer insulating film **618**, including within recess **620**.
10 Such a step can include depositing a layer of Ti to a thickness of within the range of about 50 Å to about 1000 Å, preferably about 200 Å. A third conductive layer **624** should not be construed as being limited to any particular material. Further, portions of a third conductive layer **624** not serving as a capacitor plate may interconnect other circuit elements (by way contacts, vias or the like).

15 In the example of FIG. 6H, the illustrated third conductive layer **624** can provide a common electrical connection between two capacitor structures (**614-b** and **614-c**). Accordingly, in this example, a third conductive layer **624** can form an intermediate node of two series-connected capacitor structures **614-b** and **614-c**.

A method **500** can include a CMP step that removes portions of the third
20 conductive layer outside of recess **620** (step **520**).

A semiconductor device following a step **520** is shown in FIG. 6I. Such a CMP step can further isolate a resulting portion of third conductive layer, to thereby form a capacitor plate portion **624'**. A CMP polishing step can include the removal of about of

200 Å to about 4000 Å, preferably about 800 Å. In this way, a resulting capacitor plate portion **624'** can be self-aligned with respect to the capacitor open mask. In one particular configuration, second conductive layer portions (**622-b** and **622-c**) can be connected through resulting capacitor plate portion **624'** to form an intermediate node of a built in capacitor, while corresponding first conductive layer portions (**608-b** and **608-c**) can form connections to the SRAM cell storage nodes.

Next, an interlayer dielectric can be deposited (step **522**).

As shown in FIG. 6J, a step **522** can result in an interlayer dielectric **626** that covers capacitor plate portion **624'**, and thus insulates the structure from overlying conductive layers. An interlayer dielectric **626** may be deposited silicon oxide having a thickness in the range of about 40 Å to about 1000 Å, preferably about 200 Å. After being deposited, an interlayer dielectric **626** could be subject to a planarization step.

As represented by FIG. 6K, a semiconductor device can be further processed to form additional interconnection layers and/or structures. FIG. 6K shows the formation of upper layers through which a metal contact **628** may be formed. As but one example, such upper layers can include a layer of silicon nitride **630** and a layer of titanium **632**. Even more particularly, a layer of silicon nitride can be deposited to a thickness of about 20 Å to about 300 Å, preferably about 80 Å. This can be followed by the deposition of layer of titanium having a thickness of about 80 Å to about 1500 Å, preferably about 300 Å. A contact etch mask can then be formed, followed by a contact etch step which can form an opening through layers **630** and **632**. Metal contact **628** may then be formed within a resulting opening.

Subsequent conventional processing steps may then be followed to complete a

semiconductor device.

In one particular arrangement, a soft-error rate for a semiconductor device may be reduced including an additional rectangular capacitor layer can be included by patterning a third conductive layer according to a capacitor mask pattern. Such a
5 patterned third conductive layer can be aligned with lower local interconnect layers to thereby form a built-in capacitor. One particular example of such an arrangement is shown in FIGS. 7A and 7B.

FIG. 7A is top plan view showing different integrated circuit layers of a six transistor SRAM cell. FIG. 7B is a side cross sectional view taken along line B-B of
10 FIG. 7A.

FIG. 7A illustrates a six transistor SRAM cell **700** that includes a first active region **702** connected to a low power supply contact **704**, and a second active region **706** connected to a high power supply contact **708**. A first gate layer portion **710** is formed over the active regions (**702** and **706**) to thereby form n-channel and p-channel
15 transistors of one inverter. Similarly, a second gate layer portion **712** is formed over the active regions (**702** and **706**) to thereby form n-channel and p-channel transistors of another inverter.

FIG. 7A also includes a first interconnect wiring including wiring portions **714** and **716**. Such wiring portions can "cross-couple" the inverters of the SRAM cell **700** by way
20 of local contacts **718-a** to **718-f**. Unlike conventional SRAM configurations, wiring portions **714** and **716** can have a structure that includes at least a bottom conductive layer and top conductive layer separated by a dielectric, as opposed to only one or more conductive layers.

FIG. 7A further shows, by way of darkened outline, a capacitor plate portion **720**, which in this particular example has a rectangular shape. A capacitor plate portion **720** can be formed over, and in contact with a top conductive layer of wiring portions **714** and **716**.

5 FIG. 7B illustrates an electrical connection between a capacitor plate portion **720** and a top conductive layer of wiring portions **714** and **716**. FIG. 7B also shows connection of wiring portions **714** and **716** to gate layer portions **710** and **712**, respectively, by way of local contacts **718-e** and **718-f**.

10 In this way, a capacitor structure can be incorporated into an SRAM memory cell, and thereby reduce a soft-error rate (SER).

It is also understood that the embodiments of the invention may be practiced in the absence of an element and or step not specifically disclosed. That is, an inventive feature of the invention can be elimination of an element.

15 Accordingly, while the various aspects of the particular embodiments set forth herein have been described in detail, the present invention could be subject to various changes, substitutions, and alterations without departing from the spirit and scope of the invention.